	umber	Hits		DB	Time stamp
3		. 29	(US-6144093-\$ or US-5821611-\$ or	USPAT;	2004/05/19 10:06
			US-4935803-\$ or US-6566164-\$ or	US-PGPUB	
]	US-6528880-\$ or US-6521982-\$ or		
1.			US-6465276-\$ or US-6459147-\$ or		
ľ			US-6229196-\$ or US-6396127-\$ or US-6319755-\$ or US-6307755-\$ or		
			US-6256200-\$ or US-6255672-\$ or		
ŀ	*		US-5841197-\$ or US-6249041-\$ or]	
1			US-6249136-\$ or US-5814884-\$ or	1	
	•		US-6040626-\$ or US-5929523-\$ or		
			US-4989058-\$ or US-4199774-\$ or		'. '.
1.			US-5637922-\$ or US-5105536-\$ or	1	.]
			US-6421262-\$ or US-6282107-\$).did. or (US-20010000631-\$ or US-20030075796-\$ or		
			US-20020093094-\$).did.		
4 `		. 1	6282107.URPN.	USPAT	2004/05/19 10:00
. 5		12	("4975821" "5126931" "5331533"	USPAT	2004/05/19 10:01
1 .			"5374857" "5434768" "5734563"		
-			_"5774350" -"5805434" "5812383" -		
1			"5814884" "5886383" "5973939").PN.		
6		9 11	4989058.URPN. ("3788904" "4199774" "4250519"	USPAT	2004/05/19 10:04
' .		11	("3788904" "4199774" "4250519" "4270137" "4300152" "4300250"	USPAT	2004/05/19 10:04
1 .			"4358782" "4513309" "4633282"	,	
Ì			"4639761" "4694313").PN:		
8 .		3217	soi and mosfet	USPAT;	2004/05/19 10:06
1:	* .			US-PGPUB	
9		0	vaiable with threshold with voltage with	USPAT;	2004/05/19 10:07
			complementary with mosfet	US-PGPUB;	
10		91	threshold with voltage with complementary	EPO; JPO	2004/05/30 30 65
1) J1	with mosfet	USPAT; US-PGPUB;	2004/05/19 10:28
				EPO; JPO	
11		1532	"91" and soi	USPAT;	2004/05/19 10:08
		·		US-PGPUB;	= 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1
1				EPO; JPO	
12		10	(threshold with voltage with complementary	USPAT;	2004/05/19 10:16
			with mosfet) and soi	US-PGPUB;	
13		81	(threshold with voltage with complementary	EPO; JPO	2004/05/10 10 11
			with mosfet) not ((threshold with voltage	USPAT; US-PGPUB;	2004/05/19 10:16
			with complementary with mosfet) and soi)	EPO; JPO	
14		. 0	((threshold with voltage with	USPAT;	2004/05/19 10:17
			complementary with mosfet) not ((threshold	US-PGPUB;	
1			with voltage with complementary with	EPO; JPO	
			mosfet) and soi)) and (adjusted nearl	·	
15		45	bias) ((threshold with voltage with	HODAM	0004/05/10 10 5
- 3	*	43	complementary with mosfet) not ((threshold	USPAT;	2004/05/19 10:31
	,	,	with voltage with complementary with	US-PGPUB; EPO; JPO	
			mosfet) and soi)) and bias	DEO, OFO	
16	_	5434	threshold with voltage with mosfet	USPAT;	2004/05/19 10:28
	• •		· · · · · · · · · · · · · · · · · · ·	US-PGPUB;	1001,00,15 10.20
1.7		05011		EPO; JPO	
17		95011	threshold near3 voltage near3mosfet	USPAT;	2004/05/19 10:29
	İ			US-PGPUB;	
18		3584	threshold near3 voltage near3 mosfet	EPO; JPO USPAT;	2004/05/10 10-20
		3331		US-PGPUB;	2004/05/19 10:29
	-			EPO; JPO	
19		582	(threshold near3 voltage near3 mosfet) and	USPAT;	2004/05/19-10:30
1			(soi (silicon nearl insulation))	US-PGPUB;	
20			//hh-nh-1-1 2	EPO; JPO	
20		78	((threshold near3 voltage near3 mosfet)	USPAT;	2004/05/19-10:31
1		1	and (soi (silicon near1 insulation))) and (second near1 mosfet)	US-PGPUB;	
			(second Healt Moster)	EPO; JPO	

21		78	, , , , , , , , , , , , , , , , , , ,	USPAT;	2004/05/19 10:31
			and (soi (silicon nearl insulation))) and	US-PGPUB;	
١,		,	(second near1 mosfet)) not (((threshold	EPO; JPO	
			with voltage with complementary with		, ·
			mosfet) not ((threshold with voltage with		·
			complementary with mosfet) and soi)) and		
			bias)		
22		42	, , , , , , , , , , , , , , , , , , ,	USPAT;	2004/05/19 10:32
			and (soi (silicon nearl insulation))) and	US-PGPUB;	
		•	(second near1 mosfet)) and bias	EPO; JPO	
23		26	((((threshold near3 voltage near3 mosfet)	USPAT;	2004/05/19 10:32
1			and (soi (silicon near1 insulation))) and	US-PGPUB;	
	1		(second near1 mosfet)) and bias) and (gate	EPO; JPO	
			adj electrode)		i i
24		17	5488243.URPN.	USPAT	2004/05/19 10:35
25		1707	(threshold near3 voltage near3 mosfet)	USPAT;	2004/05/19 10:45
			and bias	US-PGPUB;	·
				EPO; JPO;	
				DERWENT	
.26	د چيد مسد د.	3.6		USPAT;	2004/05/19 10:46
			and bias) and (partial\$3 near deplet\$3)	US-PGPUB;	
		, ,		EPO; JPO;	
1	•			DERWENT	4.5
27		27	(((threshold near3 voltage near3 mosfet)	USPAT;	2004/05/19 10:58
			and bias) and (partial\$3 near deplet\$3))	US-PGPUB;	
1	:	1	not ((((threshold near3 voltage near3	EPO; JPO;	
1		1 .	mosfet) and (soi (silicon near)	DERWENT	
			insulation))) and (second near1 mosfet))		,
		1 -	and bias)		
28		1 . 0	6603175.URPN.	USPAT	2004/05/19 10:47
29		3.	("5818781" "6087893" "6160292"	USPAT	2004/05/19 10:47
			"2001/0045602").PN.	302111	2004,00,10 10.47
30	•	51	partially near3 depleted near3 SOI near3	USPAT;	2004/05/19 14:21
"		1.	MOSFET	US-PGPUB;	2004/05/19 14.21
				EPO; JPO;	
1				DERWENT	
31		43	(partially near3 depleted near3 SOI near3	USPAT;	2004/05/19 13:16
"			MOSFET) and (threshold near2 voltage)	US-PGPUB;	2004/05/19 15.10
			liberary and (enreshera hearz voreage)	EPO; JPO;	
				DERWENT	· · ·
32		. 8	6222234.URPN.	USPAT	2004/05/19 13:10
33		2	("5479033" "5827755").PN.	USPAT	2004/05/19 13:10
35		0	6222234.pn. and (bias near electrode)	USPAT;	2004/05/19 13:16
"		'	ozzazoa.pii. and (pras hear electrode)	US-PGPUB;	2004/03/13 13:16
1.				EPO; JPO;	
1:	41	1		DERWENT	
34		1	6222234.pn. and bias		2004/05/19 14:59
~ 3	*		OZZZZJI.pii. dila DIGS	USPAT; US-PGPUB;	2004/05/19 14:59
	•			EPO; JPO;	
1					, ,
36		2	"6461907"	DERWENT	2004/05/10 12:05
1 20			, UZUIJU/	USPAT;	2004/05/19 13:25
1				US-PGPUB;	Bridge Control
1				EPO; JPO;	
37		1	6461007 UDDN	DERWENT	0004/05/10 10 10
38		0	6461907.URPN.	USPAT	2004/05/19 13:26
ا عو		6	("5081058" "5145802" "5479033"	USPAT	2004/05/19 13:26
20			"5650339" "5728609" "5827755").PN.		0004/05/40 == =
39		29	5479033.URPN.	USPAT	2004/05/19 13:28
40		1	6222234.pn. and ("n-channel" (n adj	USPAT;	2004/05/19 14:20
			channel))	US-PGPUB;	
		· ·		EPO; JPO;	
		-		DERWENT	•
41		0		USPAT;	2004/05/19 14:20
1.			channel))	US-PGPUB;	
	and the second	4. 4	, and the second	EPO; JPO;	g is suggested in the suggested control of the
				DERWENT	, , , , , , , , , , , , , , , , , , , ,
42		228	(partially fully) near3 depleted near3	USPAT;	2004/05/19 14:22
			MOSFET	US-PGPUB;	
				EPO; JPO;	
	<u>. </u>		<u> </u>	DERWENT	
					

43	:	22	(partially and fully) near3 depleted near3 MOSFET	USPAT; US-PGPUB;	2004/05/19 14:59
				EPO; JPO;	
44		21		DERWENT USPAT;	2004/05/19 15:00
1		,	near3 MOSFET) and (p n)	US-PGPUB;	
		,		EPO; JPO; DERWENT	
45		128	The second secon	USPAT;	2004/05/19 14:59
			SOI	US-PGPUB;	
				EPO; JPO; DERWENT	
46		436270	45and bias	USPAT;	2004/05/19 14:59
		*		US-PGPUB; EPO; JPO;	
				DERWENT	
47		40	((partially and fully) near3 depleted near3 SOI) and bias	USPAT;	2004/05/19 14:59
			hears sory and bras	US-PGPUB; EPO; JPO;	
48		38		DERWENT	
40			(((partially and fully) near3 depleted near3 SOI) and bias) and (p n)	USPAT; US-PGPUB;	2004/05/19 15:00
			The state of the s	EPO; JPO;	· , · · ·
49		22	48not ((partially and fully) near3	DERWENT	0001/05/05
			depleted near3 MOSFET)	USPAT; US-PGPUB;	2004/05/19 15:00
1				EPO; JPO;	
50		29	((((partially and fully) near3 depleted	DERWENT USPAT;	2004/05/19 15:00
	,		near3 SOI) and bias) and (p n)) not	US-PGPUB;	2004/03/19 13:00
			((partially and fully) near3 depleted near3 MOSFET)	EPO; JPO; DERWENT	